Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	45	(US-20030107103-$ or US-20020145164-$ or US-20030006463-$ or US-20030001196-$ or US-20050095758-$ or US-20040113207-$ or US-20050242401-$ or US-20040195621-$ or US-20030111691-$ or US-20040164354-$ or US-20020084485-$ or US-20020086461-$).did. or (US-6191450-$ or US-7098512-$ or US-6764892-$ or US-6611027-$ or US-6091630-$ or US-6933526-$ or US-6936898-$ or US-6504213-$ or US-7057239-$ or US-6586807-$ or US-6121657-$ or US-6787410-$ or US-5072266-$ or US-6642540-$ or US-6310380-$ or US-5159431-$ or US-6737688-$ or US-5451799-$ or US-5936265-$ or US-6867476-$ or US-6545322-$ or US-6515331-$ or US-6720633-$ or US-6255178-$ or US-6576959-$ or US-5241205-$).did. or (US-6911701-$ or US-6919601-$ or US-6897499-$).did. or (EP-615282-$).did. or (JP-62123736-$).did. or (US-20010011753-$ or US-20030111691-$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/26 08:18
L2	460	yama.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/26 08:18
L3	2	yama.in. and gate and isolati$2	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/26 08:25
L4	18	yama.in. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/26 08:25
S1	5	"423065".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 10:11
S2	2	(("6504213") or ("6611027")).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/09 20:30

S3	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 15:58
S4	267	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:06
S5	33	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat$3) and trap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 20:43
S6	13	low adj leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat$3) and plan adj view and gate near6 length	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 20:51
S7	3027	leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:06
S8	247	trap and leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:07
S9	234	(trap and leakage and (sti shallow adj trench adj isolation) and gate adj (oxide dielectric insulat$3)) not S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:07
S10	7	(US-20040195621-$ or US-20030107103-$ or US-20030001196-$).did. or (US-6611027-$ or US-6504213-$ or US-6787410-$ or US-6091630-$).did.	US-PGPUB; USPAT	OR	OFF	2005/01/09 21:39
S11	0	(2003/0006463).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:39
S12	2	("20030006463").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 21:41

S13	2	jp-2001204272$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 22:10
S14	24	drain adj2 region near10 (separated apart spaced-apart) near10 (isolation adj structure sti shallow adj trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/09 22:11
S15	8	(US-20040195621-$ or US-20030107103-$ or US-20030001196-$ or US-20030006463-$).did. or (US-6611027-$ or US-6504213-$ or US-6787410-$ or US-6091630-$).did.	US-PGPUB; USPAT	OR	OFF	2005/01/09 23:52
S16	2991	((257/355) or (257/368) or (257/446) or (257/501) or (257/506)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/08/04 18:50
S17	9	S16 and drain near6 (separated separating separate spaced apart) near6 (sti shallow adj trench adj isolation trench adj isolation trench) and (leakage leaking leak)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/10 00:21
S18	6	"410153".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/10 00:21
S19	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 15:56
S20	2	("20010001196").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 16:00
S21	2	("20030001196").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 16:13
S22	3	("6611027").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 17:06

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S23	4547	((257/355) or (257/368) or (257/446) or (257/501) or (257/506)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/01 17:06
S24	4	S23 and rectangular near4 active adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:06
S25	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/16 15:50
S26	2	("20010001196").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/16 15:50
S27	0	("647604.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 16:56
S28	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 16:57
S29	5	(("20010001196") or ("6611027")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 16:59
S30	5	(("20030001196") or ("6611027")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:15
S31	5	"423065".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:17
S32	2	("5451799").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:26

S33	6323	(aperture opening) near3 gate and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:28
S34	1045	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:28
S35	168	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET).ti, ab,clm. and (sti locos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:29
S36	44	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET).ti, ab,clm. and (sti locos) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 11:38
S37	2	("6586807").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:51
S38	0	S37 and (opening aperture) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:43
S39	0	S37 and (opening aperture) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/26 17:43
S40	1	S37 and gate adj (insulation oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:52
S41	629	"44" and gate adj (insulation oxide) and misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 17:52
S42	2	S36 and gate adj (insulation oxide) and misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 18:14

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S43	2	S36 and gate adj (insulation oxide) and misfet and (sti locos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/26 18:14
S44	66	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab,clm. and (sti locos shallow adj trench adj isolation fox field adj oxide) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:01
S45	1	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab,clm. and (sti locos shallow adj trench adj isolation fox field adj oxide) and plan adj view and (spaced adj apart separation separated) near5 drain near5 (locos sti fox field adj oxide isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:18
S46	5	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab,clm. and (spaced adj apart separation separated) near8 drain near8 (locos sti fox field adj oxide isolation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:20
S47	1	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab,clm. and (spaced adj apart separation separated distance$1) near8 drain near8 (locos sti fox field adj oxide isolation) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:20
S48	1	(aperture opening) near3 gate.ti,ab, clm. and (MOS MOSFET MIS MISFET NMOS NMOSFET PMOS PMOSFET CMOS CMOSFET).ti,ab,clm. and (spaced adj apart separation separated distance$1) near8 drain near8 (locos sti fox field adj oxide isolation) and plan adj view and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 12:20
S49	103	(gate near6 surround$3 near6 source near6 drain) and (locos fox sti (isolation near1 trench)) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 13:57

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S50	2	("6121657").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 14:21
S51	0	S50 and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 13:57
S52	989364	S50 and gate (polysilicon silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 14:22
S53	1	S50 and gate and (polysilicon silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 14:22
S54	29	(US-20020084485-$ or US-20020145164-$ or US-20030001196-$ or US-20030006463-$ or US-20030107103-$ or US-20040113207-$ or US-20040164354-$ or US-20040195621-$ or US-20020086461-$).did. or (US-5072266-$ or US-5159431-$ or US-5241205-$ or US-5451799-$ or US-5936265-$ or US-6091630-$ or US-6191450-$ or US-6310380-$ or US-6504213-$ or US-6576959-$ or US-6586807-$ or US-6611027-$ or US-6642540-$ or US-6737688-$ or US-6764892-$ or US-6787410-$ or US-6867476-$ or US-6897499-$ or US-6121657-$).did. or (US-20010011753-$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/12/27 15:45
S55	0	S54 and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:03
S56	0	S54 and gate-induced adj drain adj leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:03

EAST Search History

S57	6	(source drain) near6 (separat$3 distance spaced adj apart) near6 (sti locos fox) and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:06
S58	0	(source drain) near6 (separat$3 distance spaced adj apart) near6 (sti locos fox) and cmos near6 (imaging imager)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:07
S59	201	(source drain) near9 (separat$3 distance spaced adj apart) near9 (sti locos fox)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:07
S60	6	(source drain) near9 (separat$3 distance spaced adj apart) near9 (sti locos fox) and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:39
S61	126	(source drain) near9 (separat$3 distance spaced adj apart) near9 (sti locos fox) and (mos mosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:08
S62	53	(source drain) near9 (separat$3 distance spaced adj apart) near9 (sti locos fox) and (mos mosfet cmos cmosfet).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:29
S63	0	diffusion adj length and mos adj transistor and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 15:29
S64	4669	((257/355) or (257/368) or (257/446) or (257/501) or (257/506)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:45
S65	0	S64 and (mos mosfet).ti,ab,clm. and (locos sti shallow adj trench adj isolation isolation field adj oxide).ti,ab, clm. and gate near6 (surround$3 aperture opening) near6 (source drain).ti,ab,clm. and (rectangular square).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:48

S66	0	S64 and (mos mosfet).ti,ab,clm. and (locos sti shallow adj trench adj isolation isolation field adj oxide).ti,ab, clm. and gate near6 (surround$3 aperture opening) near6 (source drain).ti,ab,clm. and (rectangular square) and gidl	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:48
S67	0	S64 and (mos mosfet).ti,ab,clm. and (locos sti shallow adj trench adj isolation isolation field adj oxide).ti,ab, clm. and gate near6 (surround$3 aperture opening) near6 (source drain).ti,ab,clm. and (rectangular square) and (gate adj induced adj drain adj leak$3 gidl)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/27 15:48
S68	2	("6212657").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 17:35
S69	2	("6121657").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 17:43
S70	6	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 18:10
S71	5	"423065".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 18:15
S72	2	("5451799").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 18:15
S73	7200	((257/349) or (257/355) or (257/368) or (257/374) or (257/446) or (257/501) or (257/506) or (257/e29. 007) or (257/e29.016) or (257/e29. 063) or (257/e29.28)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 18:58
S74	22	S73 and (channel near1 length) near4 (variable varied stepped step vary shape shaped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 19:56

S75	5	"617420".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 19:06
S76	22	gate adj electrode near4 shape with leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 19:07
S77	2	("6121657").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 10:44
S78	171	distance near6 (sidewall sti locos) near6 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 10:45
S79	35	distance near3 (sidewall sti locos) near3 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 10:48
S80	2	(nm ".ANG.") near3 (sidewall sti locos) near3 (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 10:53
S81	631	(257/e21.628).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 11:05
S82	0	("separatednear6drainnear6(locossti)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 11:05
S83	101	(drain source) near6 (separated distanc$2 spaced adj apart) near6 (sti locos fox)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 11:43
S84	7	(gate adj length channel adj length) near6 (gate adj array) and 257/20$1.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 11:45

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S85	920	(257/20$1.ccls. 257/211) and lattice	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 11:46
S86	542	(257/20$1.ccls. 257/211) and lattice and (distance length)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 11:48
S87	10	(257/20$1.ccls. 257/211) and lattice near4 period	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 11:49
S88	385	(257/20$1.ccls. 257/211) and (sti locos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 11:50
S89	26	(257/20$1.ccls. 257/211) and (sti locos) near6 (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 11:54
S90	1210	257/506.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 12:08
S91	4	baliga.in. and unit adj cell and lateral adj2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 12:24
S92	2	("6781194").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 12:26
S93	2	("5637898").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/07 14:03
S94	0	("647604.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 14:42

S95	7	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 14:42
S96	2	"6121657".pn. and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 12:14
S97	6	"647704".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 12:25
S98	7	"647604".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 12:54
S99	8	(("20030001196") or ("6611027") or ("20030006463") or ("6121657")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 12:59
S100	3	("6611027").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 13:00
S101	0	("423065.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 13:00
S102	2	("20030001196").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 14:46
S103	2	("6586807").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 14:47
S104	2	"20010011753".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 15:28

S10 5	1964	(leakage leak).ti,ab,clm. and MOSFET. ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 15:28
S10 6	2177	(leakage leak).ti,ab,clm. and MOSFET. ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 15:28
S10 7	215	(leakage leak).ti,ab,clm. and MOSFET. ti,ab,clm. and "257"/$7.ccls.	USPAT	OR	ON	2006/12/24 15:49
S10 8	370	(257/297).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 15:49
S10 9	8552	((257/297) or (257/350) or (257/351) or (257/349) or (257/368) or (257/374) or (257/446) or (257/501) or (257/506) or (257/547) or (257/620) or (257/e29.007) or (257/e29.016) or (257/e29.017) or (257/e29.063) or (257/e29.28)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 17:34
S11 0	3	S109 and (mos mosfet) and (leakage leaking leak) and (gate near6 (overlap$4 cover$3) near6 interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 15:55
S11 1	3	S109 and (mos mosfet) and (leakage leaking leak) and (gate near6 (overlap$4 cover$3) near6 interface) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 16:00
S11 2	370	257/297.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 16:00
S11 3	802	S109 and (leakage leak leaking) and plan adj view	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 16:01
S11 4	273	S109 and (leakage leak leaking) and plan adj view and gate near10 (overlapping overlap interface boundary)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 16:02

S11 5	1	"6774733".PN.	USPAT; USOCR	OR	OFF	2006/12/24 16:06
S11 6	1	"6911701".PN.	USPAT; USOCR	OR	OFF	2006/12/24 16:26
S11 7	501	(257/374).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/24 16:59
S11 8	344	(257/374).CCLS.	USPAT	OR	OFF	2006/12/24 17:00
S11 9	8	S109 and (MOS MOSFET field adj effect adj transistor).clm. and (gate near7 (overlap overlapping cover covering) near7 (insulati$2 isolati$2 locos fox sti shallow adj trench)).clm. and gate near7 (window opening aperture hole).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 17:46
S12 0	0	(hopper.in. lindorfer.in. vaschenko.in. national adj semiconductor.as.) and (MOS MOSFET field adj effect adj transistor).clm. and (gate near7 (overlap overlapping cover covering) near7 (insulati$2 isolati$2 locos fox sti shallow adj trench)).clm. and gate near7 (window opening aperture hole).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/24 17:47

Inv Name Search: 12 pp. (Ht..)
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Inventor Name Search Result

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Last Name = HOPPER
First Name = PETER

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09351068	Not Issued	161	07/09/1999	SEMI-SOI PROCESS	HOPPER, PETER
09851280	6586317	150	05/08/2001	METHOD OF FORMING A ZENER DIODE IN A NPN AND PNP BIPOLAR PROCESS FLOW THAT REQUIRES NO ADDITIONAL STEPS TO SET THE BREAKDOWN VOLTAGE	HOPPER, PETER
09888248	6498373	150	06/22/2001	ESD PROTECTION CMOS STRUCTURE WITH DYNAMIC SUBSTRATE CONTROL	HOPPER, PETER
09960825	Not Issued	160	09/21/2001	Low process sensitive dynamic bi-polar ESD protection circuit	HOPPER, PETER
09960882	Not Issued	61	09/21/2001	Method and structure for avoiding hot carrier degradation and soft leakage damage to ESD protection circuit	HOPPER, PETER
10283810	6639784	150	10/30/2002	WEDGE-SHAPED HIGH DENSITY CAPACITOR AND METHOD OF MAKING THE CAPACITOR	HOPPER, PETER
10341040	Not Issued	161	01/13/2003	High-Q toroidal on-chip inductor	HOPPER, PETER
10385869	Not Issued	161	03/10/2003	Zener Diode Formed Adjacent to a Bipolar Transistor	HOPPER, PETER
11196899	Not Issued	41	08/04/2005	High-Q toroidal on-chip inductor	HOPPER, PETER
60136474	Not Issued	159	05/28/1999	SEMI SOI PROCESS	HOPPER, PETER
60599711	Not Issued	159	08/06/2004	High-Q toroidal on-chip inductor	HOPPER, PETER
09987805	6520722	150	11/09/2001	ASYMMETRICAL CUTTING TOOL TOOTH FORM	HOPPER, PETER B.
60796040	Not Issued	20	04/28/2006	Enhanced performance bandsaw blade toothform pattern	HOPPER, PETER B.

09219217	Not Issued	161	12/22/1998	CUTTING TOOL TOOTH FORM	HOPPER, PETER B.
09358211	Not Issued	161	10/15/1999	ASYMMETRICAL CUTTING TOOL TOOTH FORM	HOPPER, PETER B.
60067726	Not Issued	159	12/08/1997	DISPOSABLE KNIFE SYSTEM	HOPPER, PETER B.
60068652	Not Issued	159	12/23/1997	CUTTING TOOL TOOTH FORM	HOPPER, PETER B.
09896825	6598509	150	06/29/2001	CUTTING TOOL TOOTH FORM INCLUDING SET TEETH WITH SURFACE FEATURES AND METHOD OF MAKING SAME	HOPPER, PETER BLAUVELT
10429280	Not Issued	160	05/02/2003	Cutting tool tooth form including set teeth with surface features and method of making same	HOPPER, PETER BLAUVELT
09546515	Not Issued	161	04/11/2000	Radiation hardened NMOS transistor structure and method of manufacture	HOPPER, PETER J.
09614338	6362080	150	07/11/2000	Formation of a vertical junction through process simulation based optimization of implant doses and energies	HOPPER, PETER J.
09617420	6515331	150	07/17/2000	MOSFET STRUCTURE FOR USE IN ESD PROTECTION DEVICES	HOPPER, PETER J.
09658743	6355959	150	09/11/2000	GATE ELECTRODE CONTROLLABLE ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE HAVING A MOSFET WITH SOURCE DRAIN REGIONS IN SEPARATE WELLS	HOPPER, PETER J.
09660386	7067852	150	09/12/2000	ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE	HOPPER, PETER J.
09680580	6407445	150	10/06/2000	MOSFET-BASED ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE WITH A FLOATING HEAT SINK	HOPPER, PETER J.
09690558	6560081	150	10/17/2000	ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUIT	HOPPER, PETER J.
09690580	6777784	150	10/17/2000	BIPOLAR TRANSISTOR-BASED ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE WITH A HEAT SINK	HOPPER, PETER J.
09767934	6667867	150	01/23/2001	STABLE BJT ELECTROSTATIC DISCHARGE PROTECTION	HOPPER, PETER J.

				CLAMP	
09768033	6433368	150	01/22/2001	LVTSCR WITH A HOLDING VOLTAGE THAT IS GREATER THAN A DC BIAS VOLTAGE ON A TO-BE-PROTECTED NODE	HOPPER, PETER J.
09769084	6492859	150	01/24/2001	ADJUSTABLE ELECTROSTATIC DISCHARGE PROTECTION CLAMP	HOPPER, PETER J.
09782389	6541801	150	02/12/2001	TRIAC WITH A HOLDING VOLTAGE THAT IS GREATER THAN THE DC BIAS VOLTAGES THAT ARE ON THE TO-BE-PROTECTED NODES	HOPPER, PETER J.
09816287	6946690	150	03/21/2001	HIGH HOLDING VOLTAGE ESD PROTECTION STRUCTURE AND METHOD	HOPPER, PETER J.
09866148	6653716	150	05/24/2001	VARACTOR AND METHOD OF FORMING A VARACTOR WITH AN INCREASED LINEAR TUNING RANGE	HOPPER, PETER J.
09896681	6822294	150	06/29/2001	HIGH HOLDING VOLTAGE LVTSCR	HOPPER, PETER J.
09931477	6586302	150	08/16/2001	METHOD OF USING TRENCHING TECHNIQUES TO MAKE A TRANSISTOR WITH A FLOATING GATE	HOPPER, PETER J.
10000661	6528844	150	10/31/2001	SPLIT-GATE FLASH MEMORY CELL WITH A TIP IN THE MIDDLE OF THE FLOATING GATE	HOPPER, PETER J.
10025079	6645854	150	12/19/2001	FORMATION OF A VERTICAL JUNCTION THROUGH PROCESS SIMULATION BASED OPTIMIZATION OF IMPLANT DOSES AND ENERGIES	HOPPER, PETER J.
10079336	6894881	150	02/19/2002	ESD PROTECTION METHODS AND DEVICES USING ADDITIONAL TERMINAL IN THE DIODE STRUCTURES	HOPPER, PETER J.
10097283	Not Issued	161	03/12/2002	ESD protection snapback structure for overvoltage self-protecting I/O cells	HOPPER, PETER J.
10097388	6660602	150	03/12/2002	STAND-ALONE TRIGGERING STRUCTURE FOR ESD PROTECTION OF HIGH VOLTAGE CMOS	HOPPER, PETER J.
10121183	6717219	150	04/12/2002	HIGH HOLDING VOLTAGE ESD	HOPPER, PETER J.

				PROTECTION STRUCTURE FOR BICMOS TECHNOLOGY	
10121514	6784029	150	04/12/2002	BI-DIRECTIONAL ESD PROTECTION STRUCTURE FOR BICMOS TECHNOLOGY	HOPPER, PETER J.
10134805	6933588	150	04/29/2002	HIGH PERFORMANCE SCR-LIKE BJT ESD PROTECTION STRUCTURE	HOPPER, PETER J.
10173911	6844585	150	06/17/2002	CIRCUIT AND METHOD OF FORMING THE CIRCUIT HAVING SUBSURFACE CONDUCTORS	HOPPER, PETER J.
10210941	6690069	150	08/02/2002	LOW VOLTAGE COMPLEMENT ESD PROTECTION STRUCTURE	HOPPER, PETER J.
10210942	6720624	150	08/02/2002	LVTSCR-LIKE STRUCTURE WITH INTERNAL EMITTER INJECTION CONTROL	HOPPER, PETER J.
10210943	7023029	150	08/02/2002	COMPLEMENTARY VERTICAL SCRS FOR SOI AND TRIPLE WELL PROCESSES	HOPPER, PETER J.
10210948	7057215	150	08/02/2002	PMOS BASED LVTSCR AND IGBT-LIKE STRUCTURE	HOPPER, PETER J.
10210949 ✓(ESD).	Not Issued	61	08/02/2002	Snapback NMOS ESD protection structure with comb-like ballasting region	HOPPER, PETER J.
10219211	6660537	150	08/15/2002	METHOD OF INDUCING MOVEMENT OF CHARGE CARRIERS THROUGH A SEMICONDUCTOR MATERIAL	HOPPER, PETER J.

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Last Name = LINDORFER
First Name = PHILIPP

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09546515 V (a/o)	Not Issued	161	04/11/2000	Radiation hardened NMOS transistor structure and method of manufacture	LINDORFER, PHILIPP
09895803	6720592	150	06/29/2001	APPARATUS FOR HIGH SENSITIVITY, LOW LAG, HIGH VOLTAGE SWING IN A PIXEL CELL WITH AN ELECTRONIC SHUTTER	LINDORFER, PHILIPP
09950121	6534759	150	09/10/2001	VERTICAL PHOTODETECTOR WITH IMPROVED PHOTOCARRIER SEPARATION AND LOW CAPACITANCE	LINDORFER, PHILIPP
10173911	6844585	150	06/17/2002	CIRCUIT AND METHOD OF FORMING THE CIRCUIT HAVING SUBSURFACE CONDUCTORS	LINDORFER, PHILIPP
10219211	6660537	150	08/15/2002	METHOD OF INDUCING MOVEMENT OF CHARGE CARRIERS THROUGH A SEMICONDUCTOR MATERIAL	LINDORFER, PHILIPP
10219836	6646318	150	08/15/2002	BANDGAP TUNED VERTICAL COLOR IMAGER CELL	LINDORFER, PHILIPP
10255789 V (a/o.)	Not Issued	161	09/25/2002	Semiconductor-based spectrum analyzer	LINDORFER, PHILIPP
10283810	6639784	150	10/30/2002	WEDGE-SHAPED HIGH DENSITY CAPACITOR AND METHOD OF MAKING THE CAPACITOR	LINDORFER, PHILIPP
10284761	6864582	150	10/31/2002	SEMICONDUCTOR INTERCONNECT AND METHOD OF PROVIDING INTERCONNECT USING A CONTACT REGION	LINDORFER, PHILIPP
10285235	6707117	150	10/31/2002	SEMICONDUCTOR INTERCONNECTS AND METHOD OF PROVIDING INTERCONNECTS USING SILICIDE EXCLUSION	LINDORFER, PHILIPP

10355904	7057174	150	01/30/2003	HIGH-SPEED PHOTON DETECTOR AND METHOD OF FORMING THE DETECTOR	LINDORFER, PHILIPP
10356423	6855968	150	01/30/2003	HIGH-SPEED PHOTON DETECTOR AND NO COST METHOD OF FORMING THE DETECTOR	LINDORFER, PHILIPP
10438482	6924167	150	05/15/2003	A BANDGAP TUNED VERTICAL COLOR IMAGER CELL	LINDORFER, PHILIPP
10609191	6933562	150	06/27/2003	POWER TRANSISTOR STRUCTURE WITH NON-UNIFORM METAL WIDTHS	LINDORFER, PHILIPP
10625961	7050314	150	07/23/2003	LVTSCR CHARGE PUMP CONVERTER CIRCUIT	LINDORFER, PHILIPP
10640963	7105373	150	08/14/2003	VERTICAL PHOTODIODE WITH HEAVILY-DOPED REGIONS OF ALTERNATING CONDUCTIVITY TYPES	LINDORFER, PHILIPP
10647602	6798641	150	08/25/2003	LOW COST, HIGH DENSITY DIFFUSION DIODE-CAPACITOR	LINDORFER, PHILIPP
10647604	Not Issued	71	08/25/2003	Ultra low leakage MOSFET transistor	LINDORFER, PHILIPP
10650000	6919588	150	08/27/2003	HIGH-VOLTAGE SILICON CONTROLLED RECTIFIER STRUCTURE WITH IMPROVED PUNCH THROUGH RESISTANCE	LINDORFER, PHILIPP
10658166	Not Issued	161	09/08/2003	Inductor with reduced cross-talk	LINDORFER, PHILIPP
10658432	6838711	150	09/08/2003	POWER MOS ARRAYS WITH NON-UNIFORM POLYGATE LENGTH	LINDORFER, PHILIPP
10658433	Not Issued	161	09/08/2003	High density integrated inductor with core	LINDORFER, PHILIPP
10659422	6797555	150	09/10/2003	DIRECT IMPLANTATION OF FLUORINE INTO THE CHANNEL REGION OF A PMOS DEVICE	LINDORFER, PHILIPP
10670139	Not Issued	161	09/24/2003	Direct fluorine implant for improved imager sensitivity	LINDORFER, PHILIPP
10683858	7037814	150	10/10/2003	SINGLE MASK CONTROL OF DOPING LEVELS	LINDORFER, PHILIPP
10689779	6958194	150	10/21/2003	IMAGER WITH IMPROVED SENSITIVITY	LINDORFER, PHILIPP
10690181	7022968	150	10/21/2003	OPTICAL SENSOR THAT MEASURES THE LIGHT OUTPUT BY THE COMBUSTION	LINDORFER, PHILIPP

				CHAMBER OF AN INTERNAL COMBUSTION ENGINE	
10716277	7023068	150	11/17/2003	METHOD OF ETCHING A LATERAL TRENCH UNDER A DRAIN JUNCTION OF A MOS TRANSISTOR	LINDORFER, PHILIPP
10728612	6852562	150	12/05/2003	COLOR IMAGER AND LOW-COST METHOD OF FORMING THE IMAGER	LINDORFER, PHILIPP
10735500	7145187	150	12/12/2003	SUBSTRATE INDEPENDENT MULITPLE INPUT BI-DIRECTIONAL ESD PROTECTION STRUCTURE	LINDORFER, PHILIPP
10818039	6940133	150	04/05/2004	INTEGRATED TRIM STRUCTURE UTILIZING DYNAMIC DOPING	LINDORFER, PHILIPP
10821286	6972457	150	04/09/2004	IMAGING CELL THAT HAS A LONG INTEGRATION PERIOD AND METHOD OF OPERATING THE IMAGING CELL	LINDORFER, PHILIPP
10821391	6972995	150	04/09/2004	IMAGING CELL WITH A NON-VOLATILE MEMORY THAT PROVIDES A LONG INTEGRATION PERIOD AND METHOD OF OPERATING THE IMAGING CELL	LINDORFER, PHILIPP
10828999	Not Issued	61	04/21/2004	Latch-up protection in integrated circuits	LINDORFER, PHILIPP
10833212	Not Issued	61	04/27/2004	Source capacitor enhancement for improved dynamic IR drop prevention	LINDORFER, PHILIPP
10838485	Not Issued	93	05/03/2004	LASER POWERED CLOCK CIRCUIT WITH A SUBSTANTIALLY REDUCED CLOCK SKEW	LINDORFER, PHILIPP
10838671	Not Issued	80	05/03/2004	Laser powered integrated circuit	LINDORFER, PHILIPP
10845454	Not Issued	41	05/13/2004	TRANSISTOR HAVING LAYOUT FOR MINIMIZING LEAKAGE CURRENT DUE TO SIDEWALL INVERSION	LINDORFER, PHILIPP
10854079	Not Issued	41	05/24/2004	Photodiode with an increased output voltage	LINDORFER, PHILIPP
10863058	7102117	150	06/08/2004	ACTIVE PIXEL SENSOR CELL WITH INTEGRATING VARACTOR AND METHOD FOR USING SUCH CELL	LINDORFER, PHILIPP

10873872	Not Issued	93	06/21/2004	REDUCING CROSS DIE VARIABILITY IN AN EEPROM ARRAY	LINDORFER, PHILIPP
10957986	Not Issued	41	10/04/2004	Single NMOS device memory cell and array	LINDORFER, PHILIPP
10958115	Not Issued	41	10/04/2004	Single snapback device memory cell and array organization and operation	LINDORFER, PHILIPP
11007565	Not Issued	30	12/08/2004	Method of forming a circuit having subsurface conductors	LINDORFER, PHILIPP
11016147	Not Issued	93	12/17/2004	METHOD AND STRUCTURE FOR ADDRESSING HOT CARRIER DEGRADATION IN HIGH VOLTAGE DEVICES	LINDORFER, PHILIPP
11060877	Not Issued	89	02/18/2005	Self-protecting transistor array	LINDORFER, PHILIPP
11076711	7113427	150	03/09/2005	NVM PMOS-CELL WITH ONE ERASED AND TWO PROGRAMMED STATES	LINDORFER, PHILIPP
11078761	Not Issued	61	03/11/2005	APPARATUS AND METHOD FOR STORING ANALOG INFORMATION IN EEPROM MEMORY	LINDORFER, PHILIPP
11079051	Not Issued	41	03/14/2005	Low voltage turn-on range snapback ESD device based upon high Vt NMOS silicon controlled rectifier	LINDORFER, PHILIPP
11109961	Not Issued	93	04/20/2005	METHOD OF FORMING A SEMICONDUCTOR STRUCTURE WITH NON-UNIFORM METAL WIDTHS	LINDORFER, PHILIPP

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inv. name srch. for Vashchenko, Vladislav.

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Last Name = VASHCHENKO
First Name = VLADISLAV

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09658743	6355959	150	09/11/2000	GATE ELECTRODE CONTROLLABLE ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE HAVING A MOSFET WITH SOURCE DRAIN REGIONS IN SEPARATE WELLS	VASHCHENKO, VLADISLAV
09660386	7067852	150	09/12/2000	ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE	VASHCHENKO, VLADISLAV
09680580	6407445	150	10/06/2000	MOSFET-BASED ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE WITH A FLOATING HEAT SINK	VASHCHENKO, VLADISLAV
09690558	6560081	150	10/17/2000	ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUIT	VASHCHENKO, VLADISLAV
09690580	6777784	150	10/17/2000	BIPOLAR TRANSISTOR-BASED ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE WITH A HEAT SINK	VASHCHENKO, VLADISLAV
09747848 ✓ ESD jr.	Not Issued	161	12/21/2000	Diode junction based electrostatic discharge (ESD) protection structure	VASHCHENKO, VLADISLAV
09767934	6667867	150	01/23/2001	STABLE BJT ELECTROSTATIC DISCHARGE PROTECTION CLAMP	VASHCHENKO, VLADISLAV
09768033	6433368	150	01/22/2001	LVTSCR WITH A HOLDING VOLTAGE THAT IS GREATER THAN A DC BIAS VOLTAGE ON A TO-BE-PROTECTED NODE	VASHCHENKO, VLADISLAV
09769084	6492859	150	01/24/2001	ADJUSTABLE ELECTROSTATIC DISCHARGE PROTECTION CLAMP	VASHCHENKO, VLADISLAV
09782389	6541801	150	02/12/2001	TRIAC WITH A HOLDING VOLTAGE THAT IS GREATER	VASHCHENKO, VLADISLAV

				THAN THE DC BIAS VOLTAGES THAT ARE ON THE TO-BE-PROTECTED NODES	
09816287	6946690	150	03/21/2001	HIGH HOLDING VOLTAGE ESD PROTECTION STRUCTURE AND METHOD	VASHCHENKO, VLADISLAV
09851280	6586317	150	05/08/2001	METHOD OF FORMING A ZENER DIODE IN A NPN AND PNP BIPOLAR PROCESS FLOW THAT REQUIRES NO ADDITIONAL STEPS TO SET THE BREAKDOWN VOLTAGE	VASHCHENKO, VLADISLAV
09866148	6653716	150	05/24/2001	VARACTOR AND METHOD OF FORMING A VARACTOR WITH AN INCREASED LINEAR TUNING RANGE	VASHCHENKO, VLADISLAV
09879415	6548868	150	06/11/2001	ESD PROTECTION CLAMP WITH INTERNAL ZENER DIODE	VASHCHENKO, VLADISLAV
09888248	6498373	150	06/22/2001	ESD PROTECTION CMOS STRUCTURE WITH DYNAMIC SUBSTRATE CONTROL	VASHCHENKO, VLADISLAV
09896284	6559507	150	06/29/2001	COMPACT BALLASTING REGION DESIGN FOR SNAPBACK N-MOS ESD PROTECTION STRUCTURE USING MULTIPLE LOCAL N+ REGION BLOCKING	VASHCHENKO, VLADISLAV
09896681	6822294	150	06/29/2001	HIGH HOLDING VOLTAGE LVTSCR	VASHCHENKO, VLADISLAV
09943826 *V (ob.)*	Not Issued	161	08/30/2001	High frequency ESD protection using LVTSCR-like structure	VASHCHENKO, VLADISLAV
09944426 *V (LVTSCR)*	Not Issued	41	08/30/2001	High holding voltage LVTSCR-like structure	VASHCHENKO, VLADISLAV
09960825 *V (ESP pr.)*	Not Issued	160	09/21/2001	Low process sensitive dynamic bi-polar ESD protection circuit	VASHCHENKO, VLADISLAV
09960882 *V (ESD)*	Not Issued	61	09/21/2001	Method and structure for avoiding hot carrier degradation and soft leakage damage to ESD protection circuit	VASHCHENKO, VLADISLAV
10033462 *V (ESD)*	Not Issued	161	12/27/2001	Triggering BJT ESD protection circuit with double collector contact	VASHCHENKO, VLADISLAV
10033579 *V (ESD)*	Not Issued	90	12/27/2001	CMOS ESD CLAMP WITH INPUT AND SEPARATE OUTPUT VOLTAGE TERMINAL FOR ESD PROTECTION	VASHCHENKO, VLADISLAV

10079336	6894881	150	02/19/2002	ESD PROTECTION METHODS AND DEVICES USING ADDITIONAL TERMINAL IN THE DIODE STRUCTURES	VASHCHENKO, VLADISLAV
10097283 V (ESD)	Not Issued	161	03/12/2002	ESD protection snapback structure for overvoltage self-protecting I/O cells	VASHCHENKO, VLADISLAV
10097388	6660602	150	03/12/2002	STAND-ALONE TRIGGERING STRUCTURE FOR ESD PROTECTION OF HIGH VOLTAGE CMOS	VASHCHENKO, VLADISLAV
10104974 V (ESD)	Not Issued	120	03/22/2002	Multi-finger ESD triggerning protection structure with positive feedback to separate substrate contact	VASHCHENKO, VLADISLAV
10121183	6717219	150	04/12/2002	HIGH HOLDING VOLTAGE ESD PROTECTION STRUCTURE FOR BICMOS TECHNOLOGY	VASHCHENKO, VLADISLAV
10121514	6784029	150	04/12/2002	BI-DIRECTIONAL ESD PROTECTION STRUCTURE FOR BICMOS TECHNOLOGY	VASHCHENKO, VLADISLAV
10134805	6933588	150	04/29/2002	HIGH PERFORMANCE SCR-LIKE BJT ESD PROTECTION STRUCTURE	VASHCHENKO, VLADISLAV
10173911	6844585	150	06/17/2002	CIRCUIT AND METHOD OF FORMING THE CIRCUIT HAVING SUBSURFACE CONDUCTORS	VASHCHENKO, VLADISLAV
10210941	6690069	150	08/02/2002	LOW VOLTAGE COMPLEMENT ESD PROTECTION STRUCTURE	VASHCHENKO, VLADISLAV
10210942	6720624	150	08/02/2002	LVTSCR-LIKE STRUCTURE WITH INTERNAL EMITTER INJECTION CONTROL	VASHCHENKO, VLADISLAV
10210943	7023029	150	08/02/2002	COMPLEMENTARY VERTICAL SCRS FOR SOI AND TRIPLE WELL PROCESSES	VASHCHENKO, VLADISLAV
10210948	7057215	150	08/02/2002	PMOS BASED LVTSCR AND IGBT-LIKE STRUCTURE	VASHCHENKO, VLADISLAV
10210949 V (ESD)	Not Issued	61	08/02/2002	Snapback NMOS ESD protection structure with comb-like ballasting region	VASHCHENKO, VLADISLAV
10234817	7115951	150	09/04/2002	LOW TRIGGERING VOLTAGE ESD PROTECTION STRUCTURE AND METHOD FOR REDUCING THE TRIGGERING VOLTAGE	VASHCHENKO, VLADISLAV

10255789	Not Issued	161	09/25/2002	Semiconductor-based spectrum analyzer	VASHCHENKO, VLADISLAV
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